

LL034BT2510G-Q1

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4-Channel Ultra Low Capacitance TVS For ESD Protection Array : 3.3V

Features

- Transient protection for high-speed data lines
IEC61000 -4-2 (ESD) $\pm 15\text{kV}$ (Air), $\pm 14\text{kV}$ (Contact).
IEC 61000-4-4 (EFT) 40A (5/50ns).
IEC 61000-4-5 (Surge) 6A (8/20 μs) .
- Qualified to AEC-Q101 standard for high reliability.
- Lead-free parts meet RoHS requirements.
- Suffix "-H" indicates halogen-free parts, ex.LL034BT2510G-Q1-H.

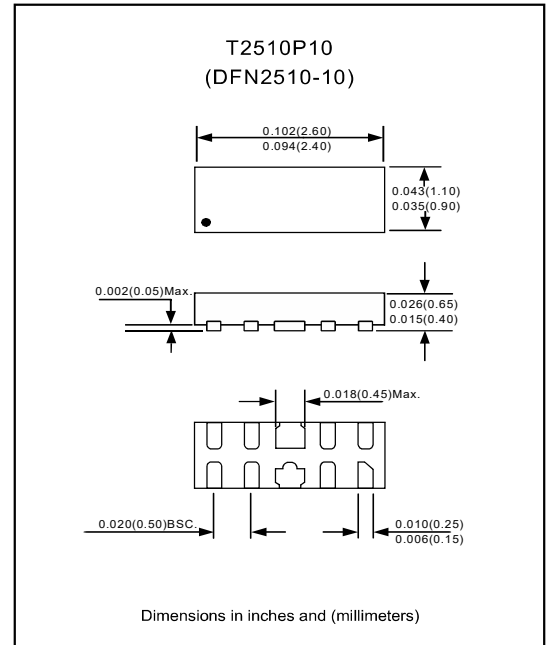
Applications

- V-by-one interface and SATA/eSATA interface.
- USB3.0/3.1 and HDMI 2.0/2.1.
- Thunderbolt interface and display ports interface.

Mechanical data

- Epoxy: UL94-V0 rated flame retardant.
- Case : Molded plastic, T2510P10 (DFN2510-10).
- Mounting Position : Any.

Package outline



Maximum ratings (at $T_A=25^\circ\text{C}$ unless otherwise noted)

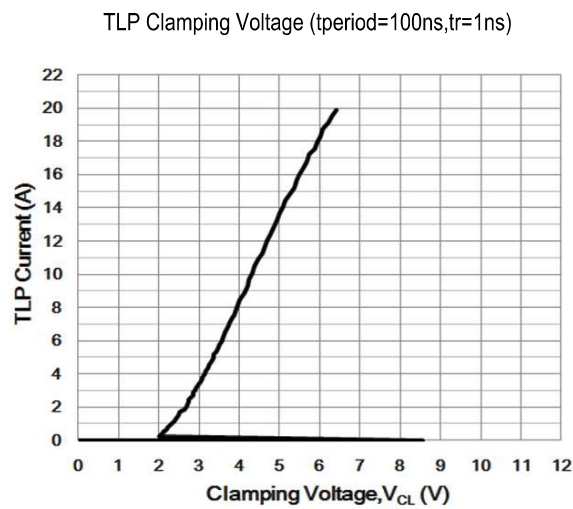
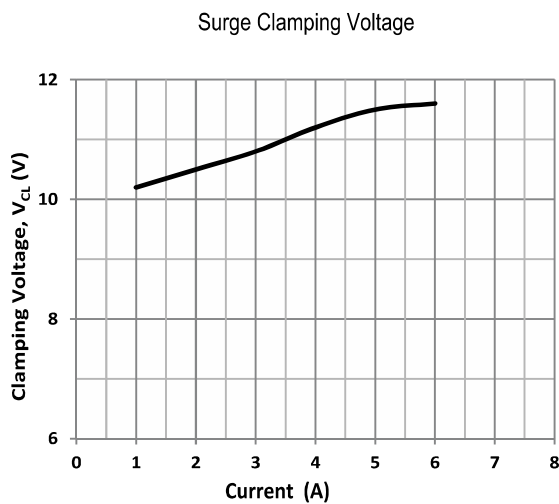
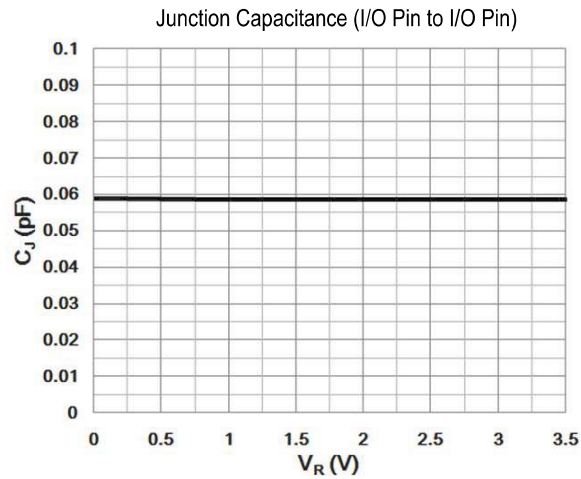
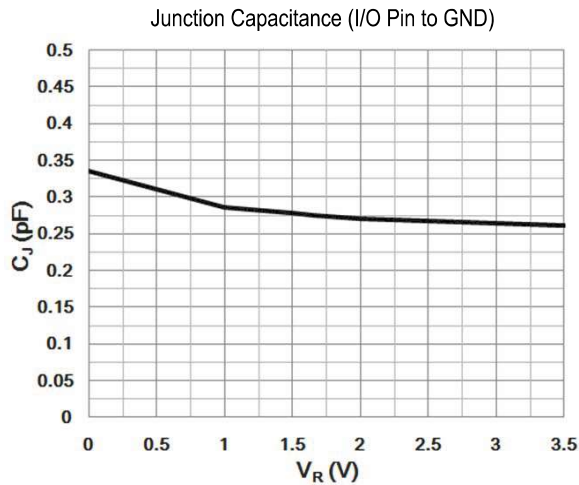
Parameter	Symbol	Value	Unit
Peak pulse current (8/20 μs)	I_{PP}	6	A
ESD per IEC61000-4-2 (Air)	V_{ESD}	± 15	kV
ESD per IEC61000-4-2 (Contact)		± 14	
Operating temperature	T_J	+105	$^\circ\text{C}$
Storage temperature range	T_{STG}	-55 to +150	$^\circ\text{C}$

Electrical characteristics (at $T_A=25^\circ\text{C}$ unless otherwise noted)

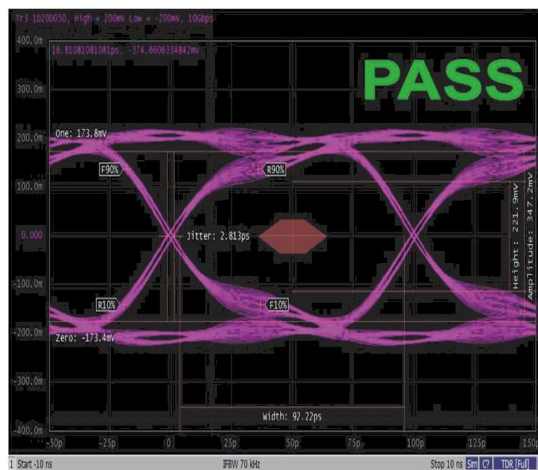
Parameter	Conditions	Symbol	Min.	Typ.	Max.	Unit
Reverse working voltage	I/O pin to GND	V_{RWM}			3.3	V
Reverse leakage current	$V_{RWM}=3.3\text{V}$, I/O pin to GND	I_R			1	μA
Reverse breakdown voltage	$I_T=1\text{mA}$, I/O pin to GND	V_{BR}	6.5		16	V
Forward voltage	$I_T=15\text{mA}$, I/O pin to GND	V_F		1		V
Surge clamping voltage	$I_{PP}=5\text{A}$, $t_p=8/20\mu\text{s}$, I/O pin to GND	V_C		11.5		V
TLP Clamping voltage	$I_{TLP}=1\text{A}$, $t_p=100\text{ns}$, $t_r=1\text{ns}$, I/O pin to GDN	V_C		2.5		V
	$I_{TLP}=16\text{A}$, $t_p=100\text{ns}$, $t_r=1\text{ns}$, I/O pin to GDN			5.5		
TLP dynamic resistance	$t_p=100\text{ns}$, $t_r=1\text{ns}$, I/O pin to GND	R_{dyn}		0.2		Ω
Junction capacitance	$V_R=1.5\text{V}$, $f=1.0\text{MHz}$, I/O pin to GND	C_J		0.28	0.33	pF
	$V_R=1.5\text{V}$, $f=1.0\text{MHz}$, between I/O pin			0.05	0.1	

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Rating and characteristic curves



10Gb/s USB3.1 Gen2 Eye Diagram with EZ0P33P2NA-A

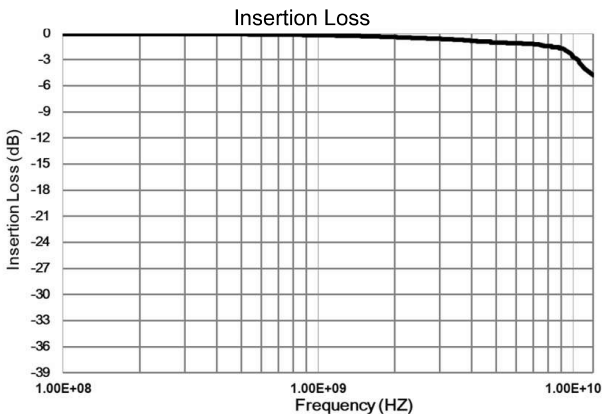


10Gb/s HDMI Eye Diagram with EZ0P33P2NA-A



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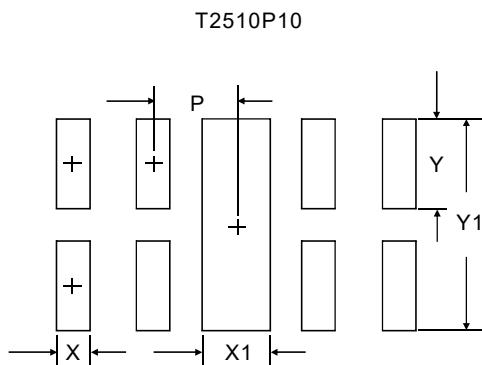
Rating and characteristic curves



Pinning information

Pin	Simplified outline	Circuit Diagram
Pin 1, 2, 4, 5 I/O Pin 3, 8 GND Pin 6, 7, 9, 10 NC	Top view Bottom view	

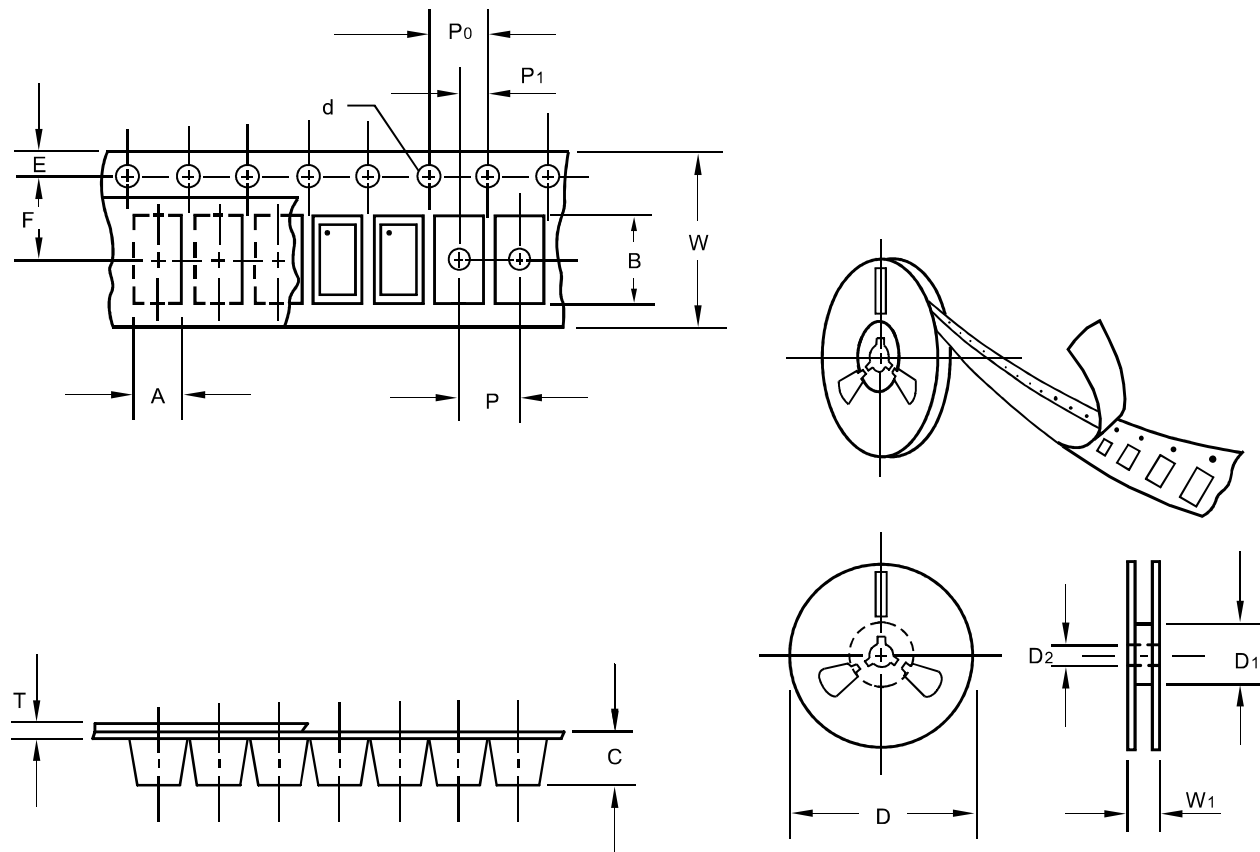
Suggested solder pad layout



DIMENSIONS		
DIM	INCHES	MILLIMETERS
P	0.022	0.55
X	0.012	0.30
X1	0.018	0.45
Y	0.027	0.68
Y1	0.067	1.70

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Packing information



unit:mm

Item	Symbol	Tolerance	T2510P10
Carrier width	A	0.1	1.20
Carrier length	B	0.1	2.70
Carrier depth	C	0.1	0.70
Sprocket hole	d	0.3	1.35
13" Reel outside diameter	D	2.0	-
13" Reel inner diameter	D1	min	-
7" Reel outside diameter	D	2.0	178.00
7" Reel inner diameter	D1	min	50.00
Feed hole diameter	D2	2.0	13.10
Sprocket hole position	E	0.1	1.75
Punch hole position	F	0.1	3.50
Punch hole pitch	P	0.1	4.00
Sprocket hole pitch	P0	0.1	4.00
Embossment center	P1	0.1	2.00
Overall tape thickness	T	0.1	0.22
Tape width	W	0.3	15.10

Note: Devices are packed in accordance with EIA standard RS-481-A and specifications listed above.

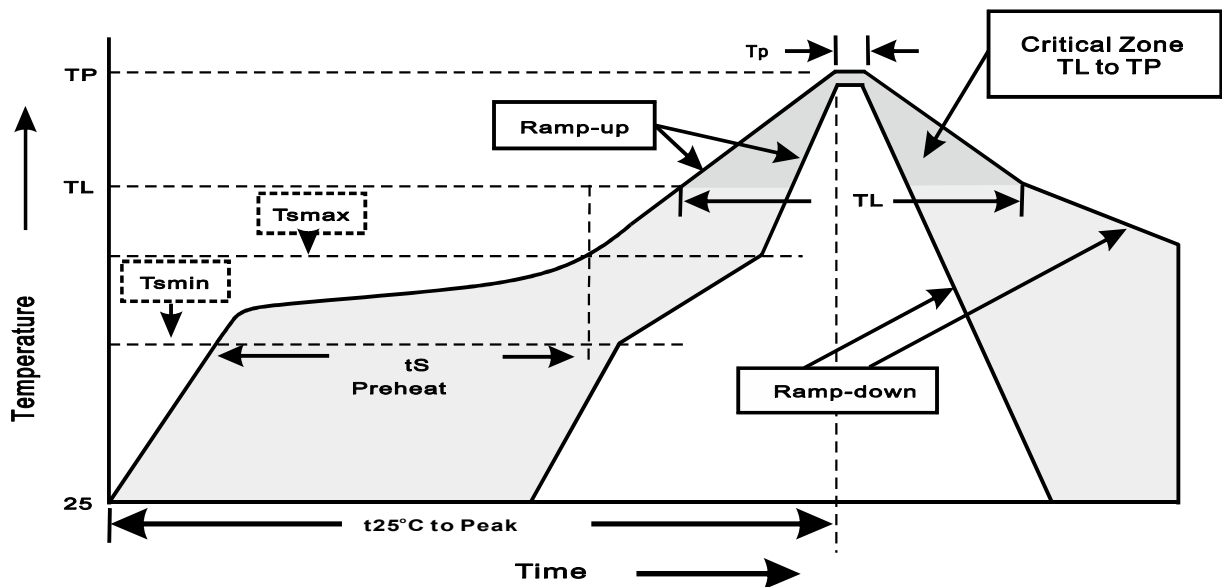
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Reel packing

PACKAGE	REEL SIZE	REEL (pcs)	COMPONENT SPACING (m/m)	BOX (pcs)	INNER BOX (m/m)	REEL DIA, (m/m)	CARTON SIZE (m/m)	CARTON (pcs)
T2510P10	7"	3,000	4.0	30,000	183*123*183	178	382*257*387	240,000

Suggested thermal profiles for soldering processes

- Storage environment: Temperature=5°C~40°C Humidity=55%±25%
- Reflow soldering of surface-mount devices



3.Reflow soldering

Profile Feature	Soldering Condition
Average ramp-up rate(T _L to T _P)	<3°C/sec
Preheat -Temperature Min(T _{min}) -Temperature Max(T _{max}) -Time(min to max)(t _s)	150°C 200°C 60~120sec
T _{max} to T _L -Ramp-upRate	<3°C/sec
Time maintained above: -Temperature(T _L) -Time(t _L)	217°C 60~260sec
Peak Temperature(T _P)	255°C-0/+5°C
Time within 5°C of actual Peak Temperature(t _P)	10~30sec
Ramp-down Rate	<6°C/sec
Time 25°C to Peak Temperature	<6minutes

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High reliability test capabilities

Item Test	Conditions	Reference
1. MSL Preconditioning	24hr bake@125°C+168hrs@85°C /85%RH+3xIR@260°C+1flux immersion+alcohol+DI H2O rinse	JESD22-A113
2. High Temperature Reverse Bias	$V_{BR}=V_{BR\ MIN}*80\%$ ($T_J=T_J\ max.$) Test Duration:1000hrs	JESD22-A108
3. High Temperature Storage Life	$T_a=150^{\circ}C$ Test Duration:1000hrs	JESD22 A-103
4. Temperature Cycle	$-55^{\circ}C(15min)$ to $150^{\circ}C(15min)$ Test Cycles:1000cycles	JESD22 A-104
5. Autoclave	$P=2atm$ $T_a=121^{\circ}C$ $RH=100\%$ Test Duration:96hrs	JESD22 A-102
6. Solderability	$245\pm5^{\circ}C$ for 5sec	J-STD-002
7. Moisture Resistance	$T_a=85^{\circ}C/85\%$ Relative humidity Test Duration:1000hrs	MIL-STD-750E METHOD 1021.2
8. Resistance To Solder Heat	$260\pm5^{\circ}C$ for 10sec	JESD22 B-106
9. High Temperature High Humidity Reverse Bias	$T_a=85^{\circ}C$, 85%RH, with device reverse biased at 80% of rated breakdown voltage up to a maximum of 100V or limit of chamber Test Duration:1000hrs	JESD22-A101